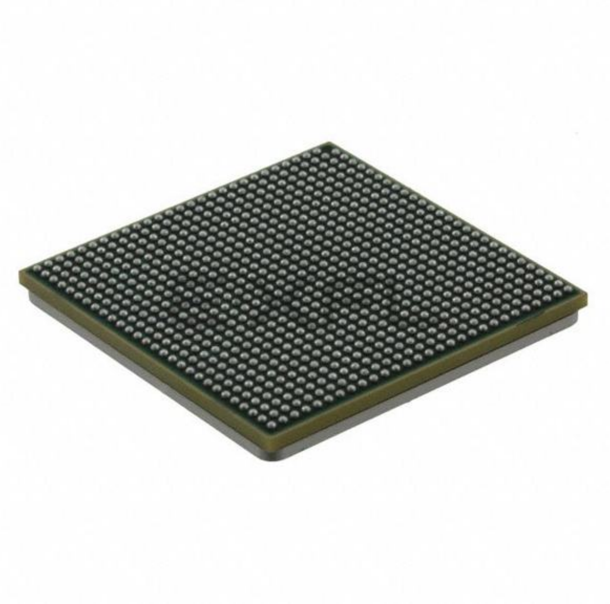

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	1.333GHz
Co-Processors/DSP	Signal Processing; SPE, Security; SEC
RAM Controllers	DDR, DDR2, SDRAM
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (4)
SATA	-
USB	-
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8548evuauj

– Up to 32 simultaneous open pages for DDR2
- Contiguous or discontiguous memory mapping
- Read-modify-write support for RapidIO atomic increment, decrement, set, and clear transactions
- Sleep mode support for self-refresh SDRAM
- On-die termination support when using DDR2
- Supports auto refreshing
- On-the-fly power management using CKE signal
- Registered DIMM support
- Fast memory access via JTAG port
- 2.5-V SSTL_2 compatible I/O (1.8-V SSTL_1.8 for DDR2)
- Support for battery-backed main memory

• Programmable interrupt controller (PIC)
- Programming model is compliant with the OpenPIC architecture.
- Supports 16 programmable interrupt and processor task priority levels
- Supports 12 discrete external interrupts
- Supports 4 message interrupts with 32-bit messages
- Supports connection of an external interrupt controller such as the 8259 programmable interrupt controller
- Four global high-resolution timers/counters that can generate interrupts
- Supports a variety of other internal interrupt sources
- Supports fully nested interrupt delivery
- Interrupts can be routed to external pin for external processing.
- Interrupts can be routed to the e500 core's standard or critical interrupt inputs.
- Interrupt summary registers allow fast identification of interrupt source.

• Integrated security engine (SEC) optimized to process all the algorithms associated with IPSec, IKE, WTLS/WAP, SSL/TLS, and 3GPP
- Four crypto-channels, each supporting multi-command descriptor chains
  – Dynamic assignment of crypto-execution units via an integrated controller
  – Buffer size of 256 bytes for each execution unit, with flow control for large data sizes
- PKEU—public key execution unit
  – RSA and Diffie-Hellman; programmable field size up to 2048 bits
  – Elliptic curve cryptography with F_2m and F(p) modes and programmable field size up to 511 bits
- DEU—Data Encryption Standard execution unit
  – DES, 3DES
  – Two key (K1, K2) or three key (K1, K2, K3)
  – ECB and CBC modes for both DES and 3DES

    - VRRP and HSRP support for seamless router fail-over
    - Up to 16 exact-match MAC addresses supported
    - Broadcast address (accept/reject)
    - Hash table match on up to 512 multicast addresses
    - Promiscuous mode
  - Buffer descriptors backward compatible with MPC8260 and MPC860T 10/100 Ethernet programming models
  - RMON statistics support
  - 10-Kbyte internal transmit and 2-Kbyte receive FIFOs
  - MII management interface for control and status
  - Ability to force allocation of header information and buffer descriptors into L2 cache
- OCeaN switch fabric
  - Full crossbar packet switch
  - Reorders packets from a source based on priorities
  - Reorders packets to bypass blocked packets
  - Implements starvation avoidance algorithms
  - Supports packets with payloads of up to 256 bytes
- Integrated DMA controller
  - Four-channel controller
  - All channels accessible by both the local and remote masters
  - Extended DMA functions (advanced chaining and striding capability)
  - Support for scatter and gather transfers
  - Misaligned transfer capability
  - Interrupt on completed segment, link, list, and error
  - Supports transfers to or from any local memory or I/O port
  - Selectable hardware-enforced coherency (snoop/no snoop)
  - Ability to start and flow control each DMA channel from external 3-pin interface
  - Ability to launch DMA from single write transaction
- Two PCI/PCI-X controllers
  - PCI 2.2 and PCI-X 1.0 compatible
  - One 32-/64-bit PCI/PCI-X port with support for speeds of up to 133 MHz (maximum PCI-X frequency in synchronous mode is 110 MHz)
  - One 32-bit PCI port with support for speeds from 16 to 66 MHz (available when the other port is in 32-bit mode)
  - Host and agent mode support
  - 64-bit dual address cycle (DAC) support
  - PCI-X supports multiple split transactions
  - Supports PCI-to-memory and memory-to-PCI streaming

- Memory prefetching of PCI read accesses
- Supports posting of processor-to-PCI and PCI-to-memory writes
- PCI 3.3-V compatible
- Selectable hardware-enforced coherency

- Serial RapidIO™ interface unit
  - Supports *RapidIO™ Interconnect Specification, Revision 1.2*
  - Both 1× and 4× LP-serial link interfaces
  - Long- and short-haul electricals with selectable pre-compensation
  - Transmission rates of 1.25, 2.5, and 3.125 Gbaud (data rates of 1.0, 2.0, and 2.5 Gbps) per lane
  - Auto detection of 1- and 4-mode operation during port initialization
  - Link initialization and synchronization
  - Large and small size transport information field support selectable at initialization time
  - 34-bit addressing
  - Up to 256 bytes data payload
  - All transaction flows and priorities
  - Atomic set/clr/inc/dec for read-modify-write operations
  - Generation of IO_READ_HOME and FLUSH with data for accessing cache-coherent data at a remote memory system
  - Receiver-controlled flow control
  - Error detection, recovery, and time-out for packets and control symbols as required by the RapidIO specification
  - Register and register bit extensions as described in part VIII (Error Management) of the RapidIO specification
  - Hardware recovery only
  - Register support is not required for software-mediated error recovery.
  - Accept-all mode of operation for fail-over support
  - Support for RapidIO error injection
  - Internal LP-serial and application interface-level loopback modes
  - Memory and PHY BIST for at-speed production test
- RapidIO-compatible message unit
  - 4 Kbytes of payload per message
  - Up to sixteen 256-byte segments per message
  - Two inbound data message structures within the inbox
  - Capable of receiving three letters at any mailbox
  - Two outbound data message structures within the outbox
  - Capable of sending three letters simultaneously
  - Single segment multicast to up to 32 devIDs
  - Chaining and direct modes in the outbox

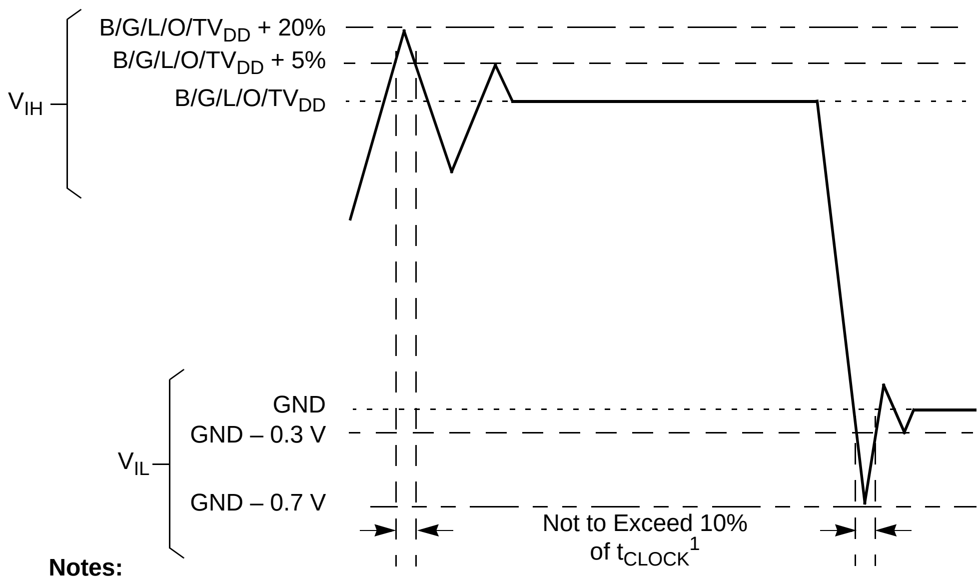
Table 2. Recommended Operating Conditions (continued)

Characteristic	Symbol	Recommended Value	Unit	Notes
Junction temperature range	Tj	0 to 105	°C	—

Notes:

1. This voltage is the input to the filter discussed in Section 22.2, "PLL Power Supply Filtering," and not necessarily the voltage at the AV_{DD} pin, which may be reduced from V_{DD} by the filter.
2. **Caution:** MV_{IN} must not exceed GV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
3. **Caution:** OV_{IN} must not exceed OV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
4. **Caution:** L/TV_{IN} must not exceed L/TV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.

The following figure shows the undershoot and overshoot voltages at the interfaces of this device.



Notes:

1. t_{CLOCK} refers to the clock period associated with the respective interface:
   For I²C and JTAG, t_{CLOCK} references SYSCLK.
   For DDR, t_{CLOCK} references MCLK.
   For eTSEC, t_{CLOCK} references EC_GTX_CLK125.
   For LBIU, t_{CLOCK} references LCLK.
   For PCI, t_{CLOCK} references PCI*n*_CLK or SYSCLK.
   For SerDes, t_{CLOCK} references SD_REF_CLK.
2. Note that with the PCI overshoot allowed (as specified above), the device does not fully comply with the maximum AC ratings and device protection guideline outlined in the PCI rev. 2.2 standard (section 4.2.2.3).

Figure 2. Overshoot/Undershoot Voltage for $GV_{DD}/OV_{DD}/LV_{DD}/BV_{DD}/TV_{DD}$

The core voltage must always be provided at nominal 1.1 V. Voltage to the processor interface I/Os are provided through separate sets of supply pins and must be provided at the voltages shown in Table 2. The input voltage threshold scales with respect to the associated I/O supply voltage. OV_{DD} and LV_{DD} based receivers are simple CMOS I/O circuits and satisfy appropriate LVCMOS type specifications. The DDR SDRAM interface uses a single-ended differential receiver referenced the externally supplied MV_{REF} signal (nominally set to $GV_{DD}/2$) as is appropriate for the SSTL2 electrical signaling standard.

2.1.3 Output Driver Characteristics

The following table provides information on the characteristics of the output driver strengths. The values are preliminary estimates.

Table 3. Output Drive Capability

Driver Type	Programmable Output Impedance (Ω)	Supply Voltage	Notes
Local bus interface utilities signals	25 25	BV_{DD} = 3.3 V BV_{DD} = 2.5 V	1
	45(default) 45(default)	BV_{DD} = 3.3 V BV_{DD} = 2.5 V	
PCI signals	25	OV_{DD} = 3.3 V	2
	45(default)		
DDR signal	18 36 (half strength mode)	GV_{DD} = 2.5 V	3
DDR2 signal	18 36 (half strength mode)	GV_{DD} = 1.8 V	3
TSEC/10/100 signals	45	L/TV_{DD} = 2.5/3.3 V	—
DUART, system control, JTAG	45	OV_{DD} = 3.3 V	—
I2C	150	OV_{DD} = 3.3 V	—

Notes:
1. The drive strength of the local bus interface is determined by the configuration of the appropriate bits in PORIMPSCR.
2. The drive strength of the PCI interface is determined by the setting of the PCI_GNT1 signal at reset.
3. The drive strength of the DDR interface in half-strength mode is at T_j = 105°C and at GV_{DD} (min).

2.2 Power Sequencing

The device requires its power rails to be applied in a specific sequence in order to ensure proper device operation. These requirements are as follows for power-up:

1. V_{DD}, AV_{DD}_*n*, BV_{DD}, LV_{DD}, OV_{DD}, SV_{DD}, TV_{DD}, XV_{DD}
2. GV_{DD}

All supplies must be at their stable values within 50 ms.

NOTE

Items on the same line have no ordering requirement with respect to one another. Items on separate lines must be ordered sequentially such that voltage rails on a previous step must reach 90% of their value before the voltage rails on the current step reach 10% of theirs.

NOTE

In order to guarantee MCKE low during power-up, the above sequencing for GV_{DD} is required. If there is no concern about any of the DDR signals being in an indeterminate state during power-up, then the sequencing for GV_{DD} is not required.

5 RESET Initialization

This section describes the AC electrical specifications for the RESET initialization timing requirements of the device. The following table provides the RESET initialization AC timing specifications for the DDR SDRAM component(s).

Table 8. RESET Initialization Timing Specifications

Parameter/Condition	Min	Max	Unit	Notes
Required assertion time of $\overline{\text{HRESET}}$	100	—	µs	—
Minimum assertion time for $\overline{\text{SRESET}}$	3	—	SYSCLKs	1
PLL input setup time with stable SYSCLK before $\overline{\text{HRESET}}$ negation	100	—	µs	—
Input setup time for POR configs (other than PLL config) with respect to negation of $\overline{\text{HRESET}}$	4	—	SYSCLKs	1
Input hold time for all POR configs (including PLL config) with respect to negation of $\overline{\text{HRESET}}$	2	—	SYSCLKs	1
Maximum valid-to-high impedance time for actively driven POR configs with respect to negation of $\overline{\text{HRESET}}$	—	5	SYSCLKs	1

Note:
1. SYSCLK is the primary clock input for the device.

The following table provides the PLL lock times.

Table 9. PLL Lock Times

Parameter/Condition	Min	Max	Unit
Core and platform PLL lock times	—	100	µs
Local bus PLL lock time	—	50	µs
PCI/PCI-X bus PLL lock time	—	50	µs

5.1 Power-On Ramp Rate

This section describes the AC electrical specifications for the power-on ramp rate requirements. Controlling the maximum power-on ramp rate is required to avoid falsely triggering the ESD circuitry. The following table provides the power supply ramp rate specifications.

Table 10. Power Supply Ramp Rate

Parameter	Min	Max	Unit	Notes
Required ramp rate for MVREF	—	3500	V/s	1
Required ramp rate for VDD	—	4000	V/s	1, 2

Note:
1. Maximum ramp rate from 200 to 500 mV is most critical as this range may falsely trigger the ESD circuitry.
2. VDD itself is not vulnerable to false ESD triggering; however, as per Section 22.2, “PLL Power Supply Filtering,” the recommended AVDD_CORE, AVDD_PLAT, AVDD_LBIU, AVDD_PCI1 and AVDD_PCI2 filters are all connected to VDD. Their ramp rates must be equal to or less than the VDD ramp rate.

6.2.2 DDR SDRAM Output AC Timing Specifications

Table 19. DDR SDRAM Output AC Timing Specifications

At recommended operating conditions.

Parameter	Symbol[1]	Min	Max	Unit	Notes
MCK[n] cycle time, MCK[*n*]/$\overline{\text{MCK}}$[*n*] crossing	t_{MCK}	3.75	6	ns	2
ADDR/CMD output setup with respect to MCK 533 MHz 400 MHz 333 MHz	t_{DDKHAS}	 1.48 1.95 2.40	 — — —	ns	3
ADDR/CMD output hold with respect to MCK 533 MHz 400 MHz 333 MHz	t_{DDKHAX}	 1.48 1.95 2.40	 — — —	ns	3
$\overline{\text{MCS}}$[*n*] output setup with respect to MCK 533 MHz 400 MHz 333 MHz	t_{DDKHCS}	 1.48 1.95 2.40	 — — —	ns	3
$\overline{\text{MCS}}$[*n*] output hold with respect to MCK 533 MHz 400 MHz 333 MHz	t_{DDKHCX}	 1.48 1.95 2.40	 — — —	ns	3
MCK to MDQS Skew	t_{DDKHMH}	–0.6	0.6	ns	4
MDQ/MECC/MDM output setup with respect to MDQS 533 MHz 400 MHz 333 MHz	t_{DDKHDS}, t_{DDKLDS}	 538 700 900	 — — —	ps	5
MDQ/MECC/MDM output hold with respect to MDQS 533 MHz 400 MHz 333 MHz	t_{DDKHDX}, t_{DDKLDX}	 538 700 900	 — — —	ps	5
MDQS preamble start	t_{DDKHMP}	$-0.5 \times t_{MCK} - 0.6$	$-0.5 \times t_{MCK} + 0.6$	ns	6

8 Enhanced Three-Speed Ethernet (eTSEC)

This section provides the AC and DC electrical characteristics for the enhanced three-speed Ethernet controller. The electrical characteristics for MDIO and MDC are specified in Section 9, "Ethernet Management Interface Electrical Characteristics."

8.1 Enhanced Three-Speed Ethernet Controller (eTSEC) (10/100/1Gb Mbps)—GMII/MII/TBI/RGMII/RTBI/RMII Electrical Characteristics

The electrical characteristics specified here apply to all gigabit media independent interface (GMII), media independent interface (MII), ten-bit interface (TBI), reduced gigabit media independent interface (RGMII), reduced ten-bit interface (RTBI), and reduced media independent interface (RMII) signals except management data input/output (MDIO) and management data clock (MDC). The RGMII and RTBI interfaces are defined for 2.5 V, while the GMII, MII, and TBI interfaces can be operated at 3.3 or 2.5 V. The GMII, MII, or TBI interface timing is compliant with the IEEE 802.3. The RGMII and RTBI interfaces follow the *Reduced Gigabit Media-Independent Interface (RGMII) Specification Version 1.3* (12/10/2000). The RMII interface follows the *RMII Consortium RMII Specification Version 1.2* (3/20/1998). The electrical characteristics for MDIO and MDC are specified in Section 9, "Ethernet Management Interface Electrical Characteristics."

8.1.1 eTSEC DC Electrical Characteristics

All GMII, MII, TBI, RGMII, RMII, and RTBI drivers and receivers comply with the DC parametric attributes specified in Table 22 and Table 23. The RGMII and RTBI signals are based on a 2.5-V CMOS interface voltage as defined by JEDEC EIA/JESD8-5.

Table 22. GMII, MII, RMII, and TBI DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit	Notes
Supply voltage 3.3 V	LV_{DD} TV_{DD}	3.13	3.47	V	1, 2
Output high voltage (LV_{DD}/TV_{DD} = min, I_{OH} = –4.0 mA)	V_{OH}	2.40	LV_{DD}/TV_{DD} + 0.3	V	—
Output low voltage (LV_{DD}/TV_{DD} = min, I_{OL} = 4.0 mA)	V_{OL}	GND	0.50	V	—
Input high voltage	V_{IH}	2.0	LV_{DD}/TV_{DD} + 0.3	V	—
Input low voltage	V_{IL}	–0.3	0.90	V	—
Input high current (V_{IN} = LV_{DD}, V_{IN} = TV_{DD})	I_{IH}	—	40	μA	1, 2, 3
Input low current (V_{IN} = GND)	I_{IL}	–600	—	μA	—

Notes:
1. LV_{DD} supports eTSECs 1 and 2.
2. TV_{DD} supports eTSECs 3 and 4.
3. The symbol V_{IN}, in this case, represents the LV_{IN} and TV_{IN} symbols referenced in Table 1 and Table 2.

Table 23. GMII, MII, RMII, TBI, RGMII, RTBI, and FIFO DC Electrical Characteristics

Parameters	Symbol	Min	Max	Unit	Notes
Supply voltage 2.5 V	LV_{DD}/TV_{DD}	2.37	2.63	V	1, 2
Output high voltage (LV_{DD}/TV_{DD} = Min, I_{OH} = –1.0 mA)	V_{OH}	2.00	LV_{DD}/TV_{DD} + 0.3	V	—
Output low voltage (LV_{DD}/TV_{DD} = Min, I_{OL} = 1.0 mA)	V_{OL}	GND –0.3	0.40	V	—
Input high voltage	V_{IH}	1.70	LV_{DD}/TV_{DD} + 0.3	V	—
Input low voltage	V_{IL}	–0.3	0.90	V	—
Input high current (V_{IN} = LV_{DD}, V_{IN} = TV_{DD})	I_{IH}	—	10	μA	1, 2, 3
Input low current (V_{IN} = GND)	I_{IL}	–15	—	μA	3

Notes:
1. LV_{DD} supports eTSECs 1 and 2.
2. TV_{DD} supports eTSECs 3 and 4.
3. Note that the symbol V_{IN}, in this case, represents the LV_{IN} and TV_{IN} symbols referenced in Table 1 and Table 2.

8.2 FIFO, GMII, MII, TBI, RGMII, RMII, and RTBI AC Timing Specifications

The AC timing specifications for FIFO, GMII, MII, TBI, RGMII, RMII, and RTBI are presented in this section.

8.2.1 FIFO AC Specifications

The basis for the AC specifications for the eTSEC's FIFO modes is the double data rate RGMII and RTBI specifications, since they have similar performances and are described in a source-synchronous fashion like FIFO modes. However, the FIFO interface provides deliberate skew between the transmitted data and source clock in GMII fashion.

When the eTSEC is configured for FIFO modes, all clocks are supplied from external sources to the relevant eTSEC interface. That is, the transmit clock must be applied to the eTSEC*n*'s TSEC*n*_TX_CLK, while the receive clock must be applied to pin TSEC*n*_RX_CLK. The eTSEC internally uses the transmit clock to synchronously generate transmit data and outputs an echoed copy of the transmit clock back out onto the TSEC*n*_GTX_CLK pin (while transmit data appears on TSEC*n*_TXD[7:0], for example). It is intended that external receivers capture eTSEC transmit data using the clock on TSEC*n*_GTX_CLK as a source- synchronous timing reference. Typically, the clock edge that launched the data can be used, since the clock is delayed by the eTSEC to allow acceptable set-up margin at the receiver. Note that there is relationship between the maximum FIFO speed and the platform speed. For more information see Section 4.5, "Platform to FIFO Restrictions."

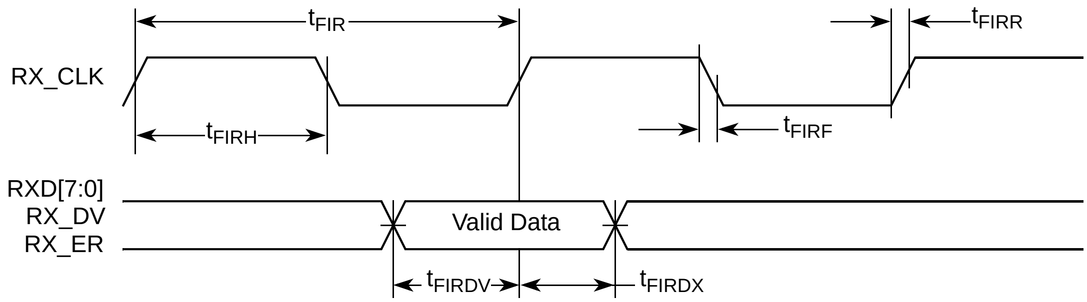


Figure 7. FIFO Receive AC Timing Diagram

8.2.2 GMII AC Timing Specifications

This section describes the GMII transmit and receive AC timing specifications.

8.2.2.1 GMII Transmit AC Timing Specifications

This table provides the GMII transmit AC timing specifications.

Table 26. GMII Transmit AC Timing Specifications

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
GMII data TXD[7:0], TX_ER, TX_EN setup time	t_{GTKHDV}	2.5	—	—	ns
GTX_CLK to GMII data TXD[7:0], TX_ER, TX_EN delay	t_{GTKHDX}	0.5	—	5.0	ns
GTX_CLK data clock rise time (20%–80%)	t_{GTXR}[2]	—	—	1.0	ns
GTX_CLK data clock fall time (80%–20%)	t_{GTXF}[2]	—	—	1.0	ns

Notes:

1. The symbols used for timing specifications follow the pattern $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, t_{GTKHDV} symbolizes GMII transmit timing (GT) with respect to the t_{GTX} clock reference (K) going to the high state (H) relative to the time date input signals (D) reaching the valid state (V) to state or setup time. Also, t_{GTKHDX} symbolizes GMII transmit timing (GT) with respect to the t_{GTX} clock reference (K) going to the high state (H) relative to the time date input signals (D) going invalid (X) or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{GTX} represents the GMII(G) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. Guaranteed by design.

9 Ethernet Management Interface Electrical Characteristics

The electrical characteristics specified here apply to MII management interface signals MDIO (management data input/output) and MDC (management data clock). The electrical characteristics for GMII, RGMII, RMII, TBI, and RTBI are specified in "Section 8, "Enhanced Three-Speed Ethernet (eTSEC)."

9.1 MII Management DC Electrical Characteristics

The MDC and MDIO are defined to operate at a supply voltage of 3.3 V. The DC electrical characteristics for MDIO and MDC are provided in this table.

Table 36. MII Management DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
Supply voltage (3.3 V)	OV_{DD}	3.13	3.47	V
Output high voltage (OV_{DD} = Min, I_{OH} = –1.0 mA)	V_{OH}	2.10	OV_{DD} + 0.3	V
Output low voltage (OV_{DD} =Min, I_{OL} = 1.0 mA)	V_{OL}	GND	0.50	V
Input high voltage	V_{IH}	2.0	—	V
Input low voltage	V_{IL}	—	0.90	V
Input high current (OV_{DD} = Max, V_{IN}[1] = 2.1 V)	I_{IH}	—	40	μA
Input low current (OV_{DD} = Max, V_{IN} = 0.5 V)	I_{IL}	–600	—	μA

Note:
1. Note that the symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

9.2 MII Management AC Electrical Specifications

This table provides the MII management AC timing specifications.

Table 37. MII Management AC Timing Specifications

At recommended operating conditions with OV_{DD} is 3.3 V ± 5%.

Parameter	Symbol[1]	Min	Typ	Max	Unit	Notes
MDC frequency	f_{MDC}	0.72	2.5	8.3	MHz	2, 3, 4
MDC period	t_{MDC}	120.5	—	1389	ns	—
MDC clock pulse width high	t_{MDCH}	32	—	—	ns	—
MDC to MDIO valid	t_{MDKHDV}	16 × t_{CCB}	—	—	ns	5
MDC to MDIO delay	t_{MDKHDX}	(16 × t_{CCB}× 8) – 3	—	(16 × t_{CCB} × 8) + 3	ns	5
MDIO to MDC setup time	t_{MDDVKH}	5	—	—	ns	—
MDIO to MDC hold time	t_{MDDXKH}	0	—	—	ns	—
MDC rise time	t_{MDCR}	—	—	10	ns	4

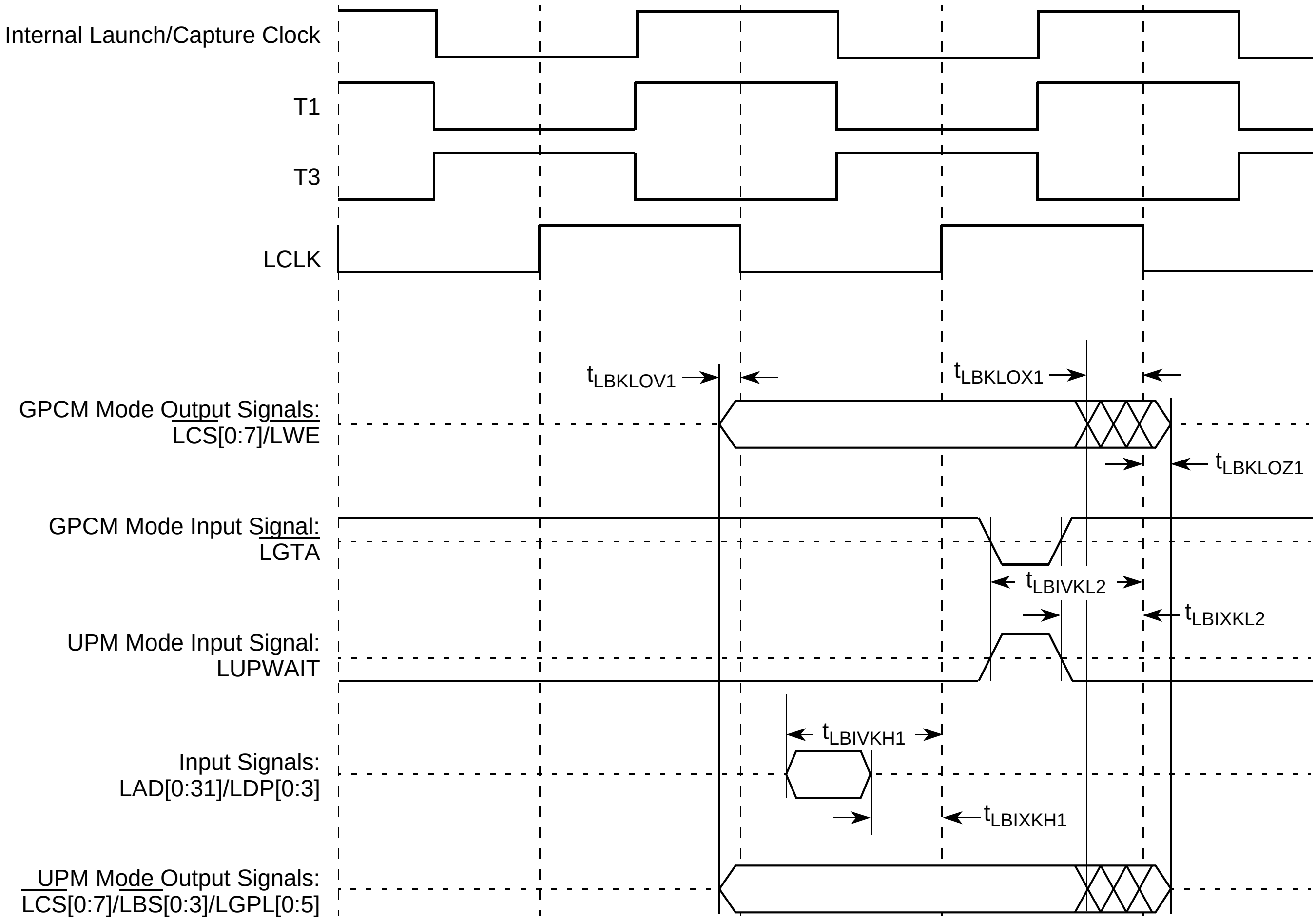


Figure 26. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 4 (PLL Bypass Mode)

Table 50. GP_{IN} DC Electrical Characteristics (2.5 V DC)

Parameter	Symbol	Min	Max	Unit
Supply voltage 2.5 V	BV_{DD}	2.37	2.63	V
High-level input voltage	V_{IH}	1.70	BV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.7	V
Input current (BV_{IN} [1] = 0 V or BV_{IN} = BV_{DD})	I_{IH}	—	10	μA

Note:
1. The symbol BV_{IN}, in this case, represents the BV_{IN} symbol referenced in Table 1.

15 PCI/PCI-X

This section describes the DC and AC electrical specifications for the PCI/PCI-X bus of the device.

Note that the maximum PCI-X frequency in synchronous mode is 110 MHz.

15.1 PCI/PCI-X DC Electrical Characteristics

This table provides the DC electrical characteristics for the PCI/PCI-X interface.

Table 51. PCI/PCI-X DC Electrical Characteristics[1]

Parameter	Symbol	Min	Max	Unit	Notes
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V	—
Low-level input voltage	V_{IL}	–0.3	0.8	V	—
Input current (V_{IN} = 0 V or V_{IN} = V_{DD})	I_{IN}	—	±5	μA	2
High-level output voltage (OV_{DD} = min, I_{OH} = –2 mA)	V_{OH}	2.4	—	V	—
Low-level output voltage (OV_{DD} = min, I_{OL} = 2 mA)	V_{OL}	—	0.4	V	—

Notes:
1. Ranges listed do not meet the full range of the DC specifications of the *PCI 2.2 Local Bus Specifications*.
2. The symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

15.2 PCI/PCI-X AC Electrical Specifications

This section describes the general AC timing parameters of the PCI/PCI-X bus. Note that the clock reference CLK is represented by SYSCLK when the PCI controller is configured for synchronous mode and by PCI*n*_CLK when it is configured for asynchronous mode.

Table 53. PCI-X AC Timing Specifications at 66 MHz (continued)

Parameter	Symbol	Min	Max	Unit	Notes
HRESET to PCI-X initialization pattern hold time	t_{PCRHIX}	0	50	ns	6, 11

Notes:

1. See the timing measurement conditions in the *PCI-X 1.0a Specification*.
2. Minimum times are measured at the package pin (not the test point). Maximum times are measured with the test point and load circuit.
3. Setup time for point-to-point signals applies to REQ and GNT only. All other signals are bused.
4. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
5. Setup time applies only when the device is not driving the pin. Devices cannot drive and receive signals at the same time.
6. Maximum value is also limited by delay to the first transaction (time for HRESET high to first configuration access, t_{PCRHFV}). The PCI-X initialization pattern control signals after the rising edge of HRESET must be negated no later than two clocks before the first FRAME and must be floated no later than one clock before FRAME is asserted.
7. A PCI-X device is permitted to have the minimum values shown for t_{PCKHOV} and t_{CYC} only in PCI-X mode. In conventional mode, the device must meet the requirements specified in PCI 2.2 for the appropriate clock frequency.
8. Device must meet this specification independent of how many outputs switch simultaneously.
9. The timing parameter t_{PCRHFV} is a minimum of 10 clocks rather than the minimum of 5 clocks in the *PCI-X 1.0a Specification.*
10. Guaranteed by characterization.
11. Guaranteed by design.

This table provides the PCI-X AC timing specifications at 133 MHz. Note that the maximum PCI-X frequency in synchronous mode is 110 MHz.

Table 54. PCI-X AC Timing Specifications at 133 MHz

Parameter	Symbol	Min	Max	Unit	Notes
SYSCLK to signal valid delay	t_{PCKHOV}	—	3.8	ns	1, 2, 3, 7, 8
Output hold from SYSCLK	t_{PCKHOX}	0.7	—	ns	1, 11
SYSCLK to output high impedance	t_{PCKHOZ}	—	7	ns	1, 4, 8, 12
Input setup time to SYSCLK	t_{PCIVKH}	1.2	—	ns	3, 5, 9, 11
Input hold time from SYSCLK	t_{PCIXKH}	0.5	—	ns	11
REQ64 to HRESET setup time	t_{PCRVRH}	10	—	clocks	12
HRESET to REQ64 hold time	t_{PCRHRX}	0	50	ns	12
HRESET high to first FRAME assertion	t_{PCRHFV}	10	—	clocks	10, 12
PCI-X initialization pattern to HRESET setup time	t_{PCIVRH}	10	—	clocks	12

— The SD_REF_CLK and $\overline{\text{SD\_REF\_CLK}}$ are internally AC-coupled differential inputs as shown in Figure 39. Each differential clock input (SD_REF_CLK or $\overline{\text{SD\_REF\_CLK}}$) has a 50-Ω termination to SGND_SRDS*n* (xcorevss) followed by on-chip AC-coupling.

— The external reference clock driver must be able to drive this termination.

— The SerDes reference clock input can be either differential or single-ended. See the differential mode and single-ended mode description below for further detailed requirements.

- The maximum average current requirement that also determines the common mode voltage range:

— When the SerDes reference clock differential inputs are DC coupled externally with the clock driver chip, the maximum average current allowed for each input pin is 8 mA. In this case, the exact common mode input voltage is not critical as long as it is within the range allowed by the maximum average current of 8 mA (see the following bullet for more detail), since the input is AC-coupled on-chip.

— This current limitation sets the maximum common mode input voltage to be less than 0.4 V (0.4 V/50 = 8 mA) while the minimum common mode input level is 0.1 V above SGND_SRDS*n* (xcorevss). For example, a clock with a 50/50 duty cycle can be produced by a clock driver with output driven by its current source from 0 to 16 mA (0–0.8 V), such that each phase of the differential input has a single-ended swing from 0 V to 800 mV with the common mode voltage at 400 mV.

— If the device driving the SD_REF_CLK and $\overline{\text{SD\_REF\_CLK}}$ inputs cannot drive 50 Ω to SGND_SRDS*n* (xcorevss) DC, or it exceeds the maximum input current limitations, then it must be AC-coupled off-chip.

- The input amplitude requirement:

— This requirement is described in detail in the following sections.

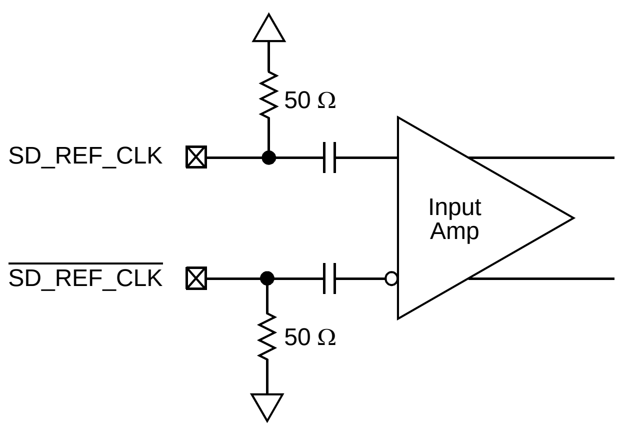


Figure 39. Receiver of SerDes Reference Clocks

16.2.2 DC Level Requirement for SerDes Reference Clocks

The DC level requirement for the SerDes reference clock inputs is different depending on the signaling mode used to connect the clock driver chip and SerDes reference clock inputs as described below:

- Differential mode

19.2 Mechanical Dimensions of the HiCTE FC-CBGA and FC-PBGA with Full Lid

The following figures show the mechanical dimensions and bottom surface nomenclature for the MPC8548E HiCTE FC-CBGA and FC-PBGA packages.

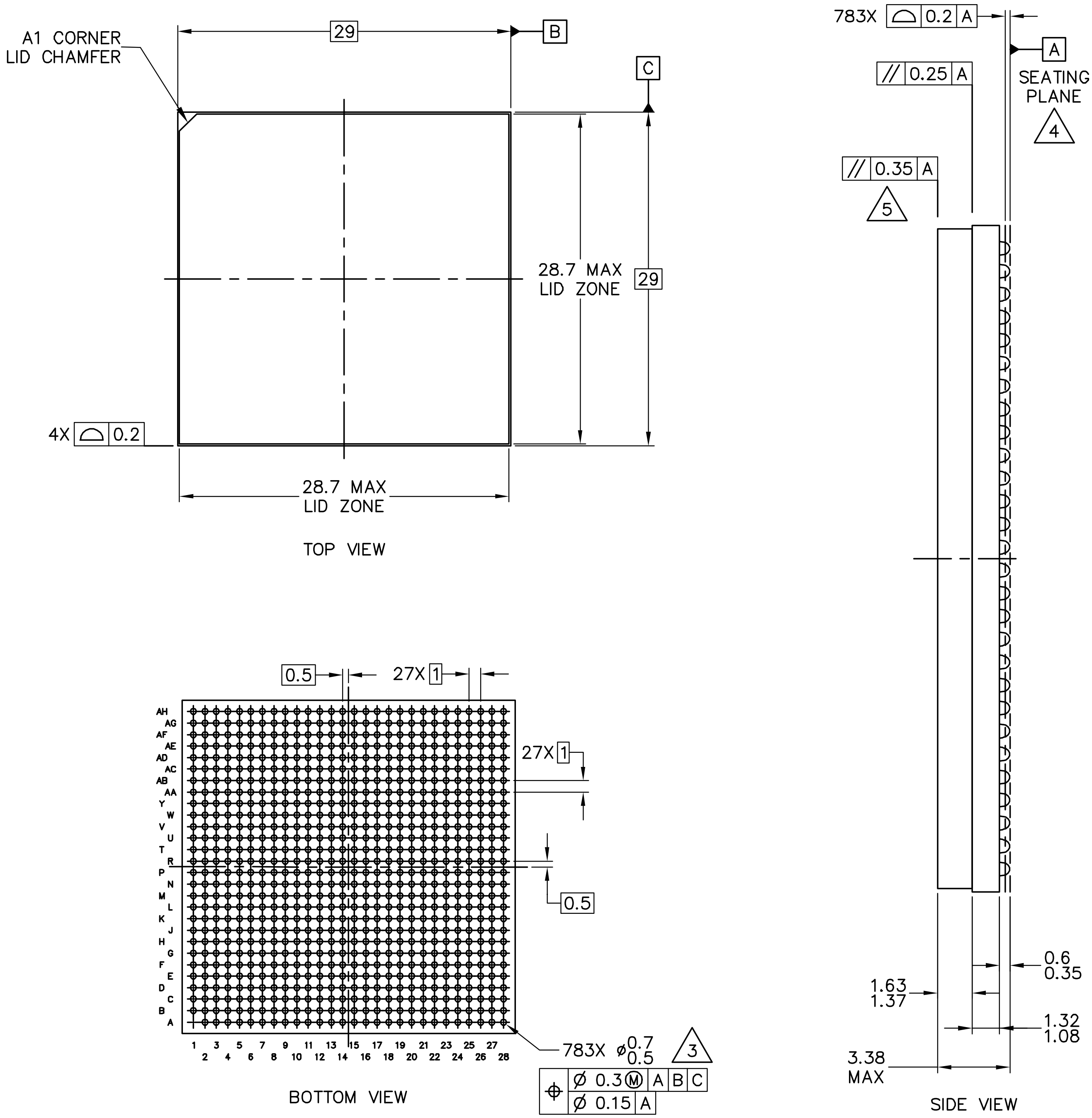


Figure 55. Mechanical Dimensions and Bottom Surface Nomenclature of the HiCTE FC-CBGA and FC-PBGA with Full Lid

Table 73. MPC8545E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
PCI1_FRAME	AE11	I/O	OV_{DD}	2
PCI1_IDSEL	AG9	I	OV_{DD}	—
PCI1_REQ64/PCI2_FRAME	AF14	I/O	OV_{DD}	2, 5, 10
PCI1_ACK64/PCI2_DEVSEL	V15	I/O	OV_{DD}	2
PCI2_CLK	AE28	I	OV_{DD}	39
PCI2_IRDY	AD26	I/O	OV_{DD}	2
PCI2_PERR	AD25	I/O	OV_{DD}	2
PCI2_GNT[4:1]	AE26, AG24, AF25, AE25	O	OV_{DD}	5, 9, 35
PCI2_GNT0	AG25	I/O	OV_{DD}	—
PCI2_SERR	AD24	I/O	OV_{DD}	2,4
PCI2_STOP	AF24	I/O	OV_{DD}	2
PCI2_TRDY	AD27	I/O	OV_{DD}	2
PCI2_REQ[4:1]	AD28, AE27, W17, AF26	I	OV_{DD}	—
PCI2_REQ0	AH25	I/O	OV_{DD}	—
DDR SDRAM Memory Interface				
MDQ[0:63]	L18, J18, K14, L13, L19, M18, L15, L14, A17, B17, A13, B12, C18, B18, B13, A12, H18, F18, J14, F15, K19, J19, H16, K15, D17, G16, K13, D14, D18, F17, F14, E14, A7, A6, D5, A4, C8, D7, B5, B4, A2, B1, D1, E4, A3, B2, D2, E3, F3, G4, J5, K5, F6, G5, J6, K4, J1, K2, M5, M3, J3, J2, L1, M6	I/O	GV_{DD}	—
MECC[0:7]	H13, F13, F11, C11, J13, G13, D12, M12	I/O	GV_{DD}	—
MDM[0:8]	M17, C16, K17, E16, B6, C4, H4, K1, E13	O	GV_{DD}	—
MDQS[0:8]	M15, A16, G17, G14, A5, D3, H1, L2, C13	I/O	GV_{DD}	—
MDQS[0:8]	L17, B16, J16, H14, C6, C2, H3, L4, D13	I/O	GV_{DD}	—
MA[0:15]	A8, F9, D9, B9, A9, L10, M10, H10, K10, G10, B8, E10, B10, G6, A10, L11	O	GV_{DD}	—
MBA[0:2]	F7, J7, M11	O	GV_{DD}	—
MWE	E7	O	GV_{DD}	—
MCAS	H7	O	GV_{DD}	—
MRAS	L8	O	GV_{DD}	—
MCKE[0:3]	F10, C10, J11, H11	O	GV_{DD}	11
MCS[0:3]	K8, J8, G8, F8	O	GV_{DD}	—
MCK[0:5]	H9, B15, G2, M9, A14, F1	O	GV_{DD}	—
MCK[0:5]	J9, A15, G1, L9, B14, F2	O	GV_{DD}	—
MODT[0:3]	E6, K6, L7, M7	O	GV_{DD}	—

Table 74. MPC8543E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
PCI1_TRDY	AG11	I/O	OV_{DD}	2
PCI1_REQ[4:1]	AH2, AG4, AG3, AH4	I	OV_{DD}	—
PCI1_REQ0	AH3	I/O	OV_{DD}	—
PCI1_CLK	AH26	I	OV_{DD}	39
PCI1_DEVSEL	AH11	I/O	OV_{DD}	2
PCI1_FRAME	AE11	I/O	OV_{DD}	2
PCI1_IDSEL	AG9	I	OV_{DD}	—
cfg_pci1_width	AF14	I/O	OV_{DD}	112
Reserved	V15	—	—	110
Reserved	AE28	—	—	2
Reserved	AD26	—	—	110
Reserved	AD25	—	—	110
Reserved	AE26	—	—	110
cfg_pci1_clk	AG24	I	OV_{DD}	5
Reserved	AF25	—	—	101
Reserved	AE25	—	—	110
Reserved	AG25	—	—	110
Reserved	AD24	—	—	110
Reserved	AF24	—	—	110
Reserved	AD27	—	—	110
Reserved	AD28, AE27, W17, AF26	—	—	110
Reserved	AH25	—	—	110
DDR SDRAM Memory Interface				
MDQ[0:63]	L18, J18, K14, L13, L19, M18, L15, L14, A17, B17, A13, B12, C18, B18, B13, A12, H18, F18, J14, F15, K19, J19, H16, K15, D17, G16, K13, D14, D18, F17, F14, E14, A7, A6, D5, A4, C8, D7, B5, B4, A2, B1, D1, E4, A3, B2, D2, E3, F3, G4, J5, K5, F6, G5, J6, K4, J1, K2, M5, M3, J3, J2, L1, M6	I/O	GV_{DD}	—
MECC[0:7]	H13, F13, F11, C11, J13, G13, D12, M12	I/O	GV_{DD}	—
MDM[0:8]	M17, C16, K17, E16, B6, C4, H4, K1, E13	O	GV_{DD}	—
MDQS[0:8]	M15, A16, G17, G14, A5, D3, H1, L2, C13	I/O	GV_{DD}	—
MDQS[0:8]	L17, B16, J16, H14, C6, C2, H3, L4, D13	I/O	GV_{DD}	—
MA[0:15]	A8, F9, D9, B9, A9, L10, M10, H10, K10, G10, B8, E10, B10, G6, A10, L11	O	GV_{DD}	—
MBA[0:2]	F7, J7, M11	O	GV_{DD}	—

21 Thermal

This section describes the thermal specifications of the device.

21.1 Thermal for Version 2.0 Silicon HiCTE FC-CBGA with Full Lid

This section describes the thermal specifications for the HiCTE FC-CBGA package for revision 2.0 silicon.

This table shows the package thermal characteristics.

Table 84. Package Thermal Characteristics for HiCTE FC-CBGA

Characteristic	JEDEC Board	Symbol	Value	Unit	Notes
Die junction-to-ambient (natural convection)	Single-layer board (1s)	$R_{\theta JA}$	17	°C/W	1, 2
Die junction-to-ambient (natural convection)	Four-layer board (2s2p)	$R_{\theta JA}$	12	°C/W	1, 2
Die junction-to-ambient (200 ft/min)	Single-layer board (1s)	$R_{\theta JA}$	11	°C/W	1, 2
Die junction-to-ambient (200 ft/min)	Four-layer board (2s2p)	$R_{\theta JA}$	8	°C/W	1, 2
Die junction-to-board	N/A	$R_{\theta JB}$	3	°C/W	3
Die junction-to-case	N/A	$R_{\theta JC}$	0.8	°C/W	4

Notes:

1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, airflow, power dissipation of other components on the board, and board thermal resistance.
2. Per JEDEC JESD51-6 with the board (JESD51-7) horizontal.
3. Thermal resistance between the die and the printed-circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
4. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1). The cold plate temperature is used for the case temperature, measured value includes the thermal resistance of the interface layer.

21.2 Thermal for Version 2.1.1, 2.1.2, and 2.1.3 Silicon FC-PBGA with Full Lid and Version 3.1.x Silicon with Stamped Lid

This section describes the thermal specifications for the FC-PBGA package for revision 2.1.1, 2.1.2, and 3.0 silicon.

This table shows the package thermal characteristics.

Table 85. Package Thermal Characteristics for FC-PBGA

Characteristic	JEDEC Board	Symbol	Value	Unit	Notes
Die junction-to-ambient (natural convection)	Single-layer board (1s)	$R_{\theta JA}$	18	°C/W	1, 2
Die junction-to-ambient (natural convection)	Four-layer board (2s2p)	$R_{\theta JA}$	13	°C/W	1, 2
Die junction-to-ambient (200 ft/min)	Single-layer board (1s)	$R_{\theta JA}$	13	°C/W	1, 2
Die junction-to-ambient (200 ft/min)	Four-layer board (2s2p)	$R_{\theta JA}$	9	°C/W	1, 2

- $\overline{\text{SD\_REF\_CLK}}$

NOTE

It is recommended to power down the unused lane through SRDSCR1[0:7] register (offset = 0xE_0F08) (this prevents the oscillations and holds the receiver output in a fixed state) that maps to SERDES lane 0 to lane 7 accordingly.

Pins V28 and M26 must be tied to XV_{DD}. Pins V27 and M25 must be tied to GND through a 300-Ω resistor.

22.11 Guideline for PCI Interface Termination

PCI termination if PCI 1 or PCI 2 is not used at all.

Option 1

If PCI arbiter is enabled during POR:

- All AD pins are driven to the stable states after POR. Therefore, all ADs pins can be floating.
- All PCI control pins can be grouped together and tied to OV_{DD} through a single 10-kΩ resistor.
- It is optional to disable PCI block through DEVDISR register after POR reset.

Option 2

If PCI arbiter is disabled during POR:

- All AD pins are in the input state. Therefore, all ADs pins need to be grouped together and tied to OV_{DD} through a single (or multiple) 10-kΩ resistor(s).
- All PCI control pins can be grouped together and tied to OV_{DD} through a single 10-kΩ resistor.
- It is optional to disable PCI block through DEVDISR register after POR reset.

22.12 Guideline for LBIU Termination

If the LBIU parity pins are not used, the following is the termination recommendation:

- For LDP[0:3]—tie them to ground or the power supply rail via a 4.7-kΩ resistor.
- For LPBSE—tie it to the power supply rail via a 4.7-kΩ resistor (pull-up resistor).